MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

Amplifier Transistors

NPN Silicon

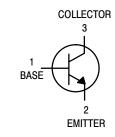
Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



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Rating	Symbol	6428LT1	6429LT1	Unit
Collector-Emitter Voltage	V _{CEO}	50	45	Vdc
Collector-Base Voltage	V _{CBO}	60	55	Vdc
Emitter-Base Voltage	V _{EBO}	6.0		Vdc
Collector Current – Continuous	Ι _C	200		mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$ Derate above 25°C	P _D	225 1.8	mW mW/⁰C
Derate above 25 C		1.0	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^{\circ}C$	PD	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.



SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



XXX = Specific Device Code MMBT6428LT1 – 1KM

- NSV/MMBT6429LT1 M1L
- M = Date Code*
- = Pb–Free Package

(Note: Microdot may be in either location) *Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT6428LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
MMBT6429LT1G	SOT–23 (Pb–Free)	3000 Tape & Reel
NSVMMBT6429LT1G	SOT–23 (Pb–Free)	3000 Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteris	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage $(I_C = 1.0 \text{ mAdc}, I_B = 0)$ $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	MMBT6428 MMBT6429 / NSVMMBT6429	V _{(BR)CEO}	50 45		Vdc
Collector – Base Breakdown Voltage $(I_C = 0.1 \text{ mAdc}, I_E = 0)$ $(I_C = 0.1 \text{ mAdc}, I_E = 0)$	MMBT6428 MMBT6429 / NSVMMBT6429	V _{(BR)CBO}	60 55		Vdc
Collector Cutoff Current (V _{CE} = 30 Vdc)		ICES	-	0.1	μAdc
Collector Cutoff Current ($V_{CB} = 30 \text{ Vdc}, I_E = 0$)		I _{CBO}	-	0.01	μAdc
Emitter Cutoff Current ($V_{EB} = 5.0 \text{ Vdc}, I_C = 0$)		I _{EBO}	-	0.01	μAdc

ON CHARACTERISTICS

DC Current Gain		h _{FE}			-
$(I_{C} = 0.01 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT6428 MMBT6429 / NSVMMBT6429		250 500	-	
$(I_{C} = 0.1 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT6428 MMBT6429 / NSVMMBT6429		250 500	650 1250	
$(I_{C} = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT6428 MMBT6429 / NSVMMBT6429		250 500	-	
$(I_{C} = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	MMBT6428 MMBT6429 / NSVMMBT6429		250 500	-	
Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 0.5 \text{ mAdc}$) ($I_C = 100 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)		V _{CE(sat)}	-	0.2 0.6	Vdc
Base-Emitter On Voltage (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc)		V _{BE(on)}	0.56	0.66	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain – Bandwidth Product ($I_C = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}, f = 100 \text{ MHz}$)	f _T	100	700	MHz
Output Capacitance (V_{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	-	3.0	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz}$)	C _{ibo}	-	8.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

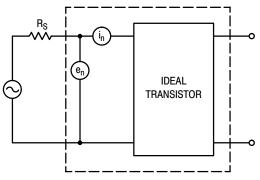


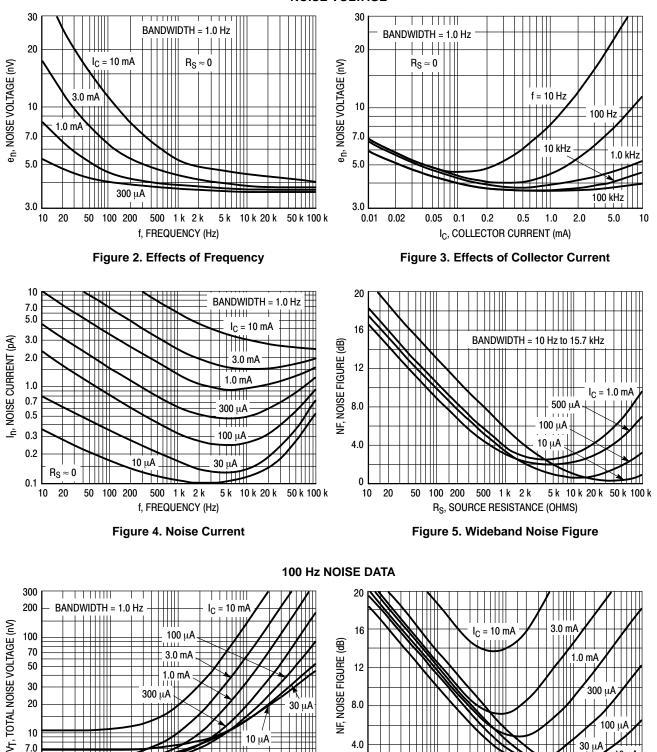
Figure 1. Transistor Noise Model

MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G

NOISE CHARACTERISTICS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

NOISE VOLTAGE





R_S, SOURCE RESISTANCE (OHMS)

100 200 500 1k 2k

300

30

100

5 k 10 k 20 k 50 k 100 k

10 µ/

8.0

4.0

٥

10 20

BANDWIDTH = 1.0 Hz

1 1 1 1 1 1 1

50

30 µA

10 μA

5 k 10 k 20 k 50 k 100 k

30

20

10

7.0

5.0

3.0

10 20 300 µA

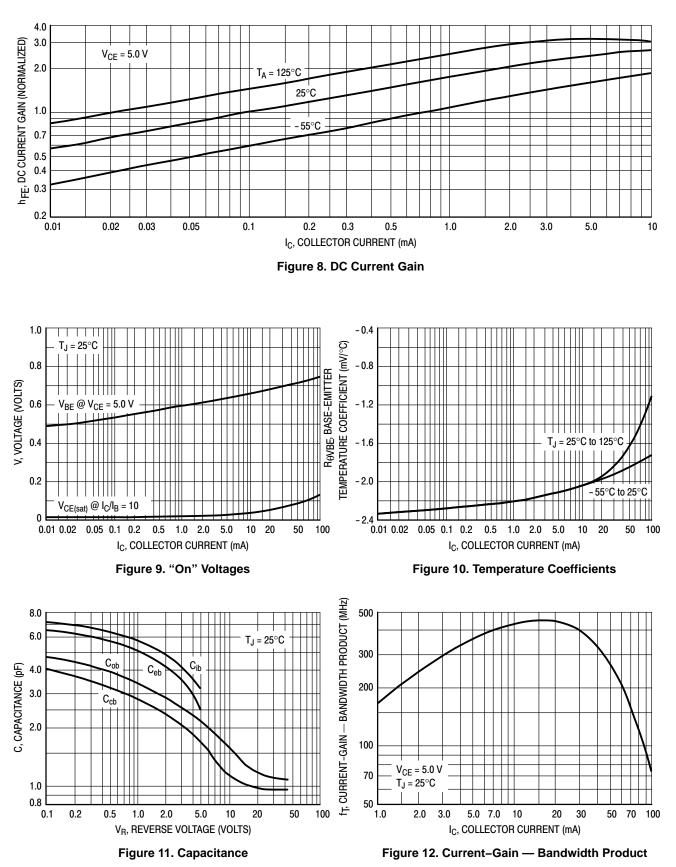
500 1 k 2 k

R_S, SOURCE RESISTANCE (OHMS)

Figure 6. Total Noise Voltage

50 100 200

MMBT6428LT1G, MMBT6429LT1G, NSVMMBT6429LT1G



MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

D

3

TOP VIEW

SIDE VIEW

Нe

DETAIL A

-3X b

onsemi



SCALE 4:1

' ل_A ____ A1___ SOT-23 (TO-236) CASE 318 ISSUE AT

0.25

-L1

DETAIL A

END VIEW

DATE 01 MAR 2023

NDTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIM	IETERS			INCHES	
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
Η _E	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

onsemi

SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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